

## RFP8N20L

### 8A, 200V, 0.600 Ohm, Logic Level, N-Channel Power MOSFET

This N-Channel enhancement mode silicon gate power field effect transistor is specifically designed for use with logic level (5V) driving sources in applications such as programmable controllers, automotive switching and solenoid drivers. This performance is accomplished through a special gate oxide design which provides full rated conduction at gate biases in the 3V to 5V range, thereby facilitating true on-off power control directly from logic circuit supply voltages.

### Ordering Information

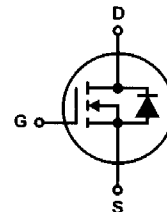
PART NUMBER	PACKAGE	BRAND
RFP8N20L	TO-220AB	RFP8N20L

NOTE: When ordering, include the entire part number.

### Features

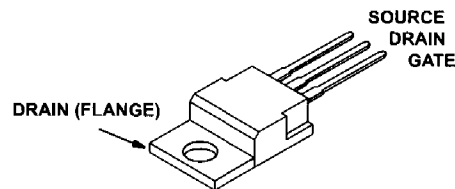
- 8A, 200V
- $r_{DS(ON)} = 0.600\Omega$
- Design Optimized for 5V Gate Drives
- Can be Driven Directly from QMOS, NMOS, TTL Circuits
- Compatible with Automotive Drive Requirements
- SOA is Power Dissipation Limited
- Nanosecond Switching Speeds
- Linear Transfer Characteristics
- High Input Impedance
- Majority Carrier Device

### Symbol



### Packaging

JEDEC TO-220AB



NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

## RFP8N20L

### Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ , Unless Otherwise Specified

	RFP8N20L	UNITS
Drain to Source Voltage (Note 1) . . . . .	200	V
Drain to Gate Voltage ( $R_{GS} = 20\text{k}\Omega$ ) (Note 1) . . . . .	200	V
Continuous Drain Current . . . . .	8	A
Pulsed Drain Current (Note 3) . . . . .	20	A
Gate to Source Voltage . . . . .	10	V
Maximum Power Dissipation . . . . .	60	W
Above $T_C = 25^\circ\text{C}$ , Derate Linearly . . . . .	0.48	W/ $^\circ\text{C}$
Operating and Storage Temperature . . . . .	-55 to 150	$^\circ\text{C}$
Maximum Temperature for Soldering		
Leads at 0.063in (1.6mm) from Case for 10s . . . . .	300	$^\circ\text{C}$
Package Body for 10s, See Techbrief 334 . . . . .	260	$^\circ\text{C}$

*CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.*

**NOTE:**

1.  $T_J = 25^\circ\text{C}$  to  $125^\circ\text{C}$ .

### Electrical Specifications $T_C = 25^\circ\text{C}$ , Unless Otherwise Specified

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Drain to Source Breakdown Voltage	$BV_{DSS}$	$I_D = 250\mu\text{A}$ , $V_{GS} = 0$	200	-	-	V
Gate to Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}$ , $I_D = 250\mu\text{A}$	1	-	2	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 0.8 \times \text{Rated } BV_{DSS}$ , $T_C = 25^\circ\text{C}$	-	-	1	$\mu\text{A}$
		$V_{DS} = 0.8 \times \text{Rated } BV_{DSS}$ , $T_C = 125^\circ\text{C}$	-	-	50	$\mu\text{A}$
Gate to Source Leakage Current	$I_{GSS}$	$V_{GS} = 10\text{V}$ , $V_{DS} = 0$	-	-	100	nA
Drain to Source On-Voltage (Note 2)	$V_{DS(ON)}$	$I_D = 8\text{A}$ , $V_{GS} = 5\text{V}$	-	-	4.8	V
Drain to Source On Resistance (Note 2)	$r_{DS(ON)}$	$I_D = 4\text{A}$ , $V_{GS} = 5\text{V}$	-	-	0.600	$\Omega$
Turn On Delay Time	$t_{d(ON)}$	$I_D = 4\text{A}$ , $V_{DD} = 50\text{V}$ , $R_G = 6.25$ , $V_{GS} = 5\text{V}$	-	15	45	ns
Rise Time	$t_r$		-	45	150	ns
Turn Off Delay Time	$t_{d(OFF)}$		-	100	135	ns
Fall Time	$t_f$		-	60	105	ns
Input Capacitance	$C_{ISS}$	$V_{GS} = 0\text{V}$ , $V_{DS} = 25\text{V}$ , $f = 1\text{MHz}$	-	-	900	pF
Output Capacitance	$C_{OSS}$		-	-	250	pF
Reverse Transfer Capacitance	$C_{RSS}$		-	-	120	pF
Thermal Resistance Junction to Case	$R_{\theta JC}$	RFP8N20L			2.083	$^\circ\text{C/W}$

### Source to Drain Diode Specifications

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Source to Drain Diode Voltage (Note 2)	$V_{SD}$	$I_{SD} = 4\text{A}$	-	-	1.4	V
Diode Reverse Recovery Time	$t_{rr}$	$I_{SD} = 4\text{A}$ , $dI_{SD}/dt = 100\text{A}/\mu\text{s}$	-	250	-	ns

**NOTES:**

2. Pulsed: pulse duration =  $300\mu\text{s}$  max, duty cycle = 2%.
3. Repetitive rating: pulse width limited by maximum junction temperature.